

BACK-END

MOS-FET

DIODE

di/dt TESTER di/dtテスター

GST650Z

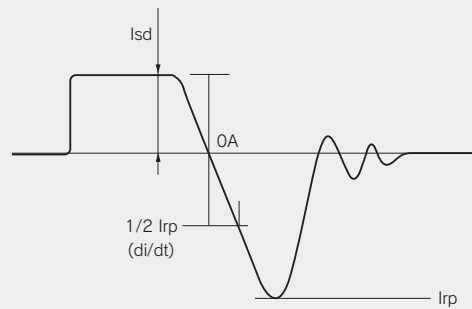
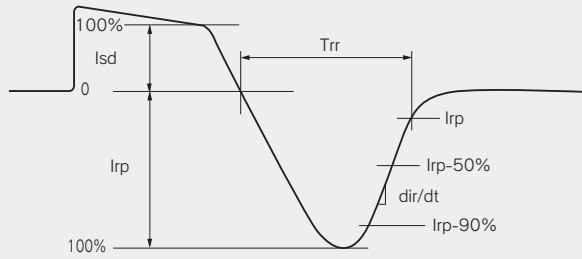
600V
500A

NEW



- GST650Z has been designed to seek and judge di/dt characteristic with software by using reverse recovery waveform of MOS-FETs and diodes or break waveform with digital oscilloscope. It has OPEN/SHORT test and driver check functions to improve reliability.
- GST650Zは、MOS-FETやダイオードの逆回復波形や破壊波形をオシロスコープから取り込み、ソフトウェアでdi/dtを求めその特性を判定します。OPEN/SHORT試験、ドライバーチェック機能もあり信頼性を向上させています。

Reference Waveform (di/dt measurement regulation [di/dt測定規定])



$$di/dt \quad [Isd \cdot (95\% \sim 0\%) \Rightarrow Irp \cdot (0\% \sim 95\%)]$$

$$Trr \quad [0 \sim Irp \cdot (95\% \sim 0\%)]$$

$$dir/dt \quad [Irp \cdot 90\% \Rightarrow Irp \cdot 50\%]$$

Isd : Diode forward current(ダイオードの順方向電流)
Irp : Irr peak current(Irrのピーク電流)

MODEL	GST650Z	
TEST ITEMS	Isd, di/dt, Irp, Trr, Vrp	
Vrr VOLTAGE	30V~599V	1V STEP
GATE VOLTAGE	ON +0V~+39.9V	0.1V STEP
	OFF -0V~-39.9V	0.1V STEP
D.U.T. BIAS	00.0V~+15.0V	0.1V STEP
	00.0V~-15.0V	0.1V STEP
GATE PULSE	ON 2.0μs~999.9μs	0.1μs STEP
	OFF 1μs~999μs	1μs STEP
di/dt TIME	1μs~99μs 1μs STEP	
Rg	0.1Ω~99.9Ω	0.1Ω STEP
Id LIMIT	1A~499A	1A STEP
PRE/POST CHECK	OPEN : Vsd(VF) > 3V	
	SHORT : Vds(VR) < Vrr Setting × 80%	
DRIVER CHECK	OPEN : Vds(SAT) > Vrr Setting × 20%	
	SHORT : Vdss < Vrr Setting × 80%	
DIMENSIONS & WEIGHT		
MAIN UNIT	430(W)×700(D)×245(H)…35kg	
HEAD BOX	1275(W)×830(D)+Safety cover×225(H)…33kg	

[Save example of measurement data]
[測定データ保存例]

